

isc Silicon NPN Power Transistors

2SD5072

DESCRIPTION

- · High Breakdown Voltage-
- : V_{CBO}= 1500V (Min)
- · High Switching Speed
- · High Reliability
- Built-in Damper Diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

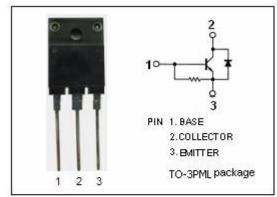


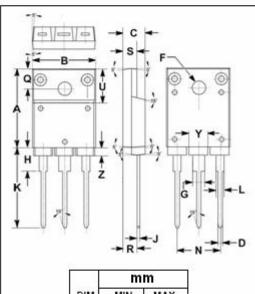
APPLICATIONS

 Designed for use in horizontal deflection circuits of colour TV receivers.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|---|---------|------------|
| V _{СВО} | Collector-Base Voltage | 1500 | V |
| Vceo | Collector-Emitter Voltage | 800 | V |
| V _{EBO} | Emitter-Base Voltage | 6 | V |
| Ic | Collector Current-Continuous | 5 | A |
| Ісм | Collector Current-Peak | 16 | Α |
| Pc | Collector Power Dissipation @T _C =25℃ | 60 | W |
| TJ | Junction Temperature | 150 | $^{\circ}$ |
| T _{stg} | Storage Temperature | -55~150 | $^{\circ}$ |





| | mm | |
|-----|-------|-------|
| DIM | MIN | MAX |
| Α | 19.90 | 20.10 |
| В | 15.75 | 16.10 |
| С | 5.50 | 5.70 |
| D | 0.90 | 1.10 |
| F | 3.30 | 3.50 |
| G | 2.90 | 3.20 |
| Н | 5.90 | 6.10 |
| J | 0.595 | 0.70 |
| K | 21.10 | 22.50 |
| L | 1.90 | 2.25 |
| N | 10.80 | 11.00 |
| 0 | 4.90 | 5.10 |
| R | 3.75 | 3.95 |
| S | 3.20 | 3.60 |
| U | 9.90 | 10.10 |
| Y | 4.20 | 4.90 |
| Z | 1.90 | 2.10 |



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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP | MAX | UNIT |
|-----------------------|--------------------------------------|--|-----|-----|-----|------|
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | I _C = 4.0A; I _B = 0.8A | | | 5.0 | V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = 4.0A ;I _B = 0.8A | | | 1.5 | V |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 4V; I _C =0 | 40 | | 200 | mA |
| I _{CBO} | Collector-Base Cutoff Current | V _{CB} =800V; I _E = 0 | | | 10 | uA |
| h _{FE} | DC Current Gain | I _C = 1A; V _{CE} = 5V | 8 | | | |
| f⊤ | Current-Gain—Bandwidth Product | I _C = 1A; V _{CE} = 10V | | 3 | | MHz |
| V _{ECF} | C-E Diode Forward Voltage | I _F = 5.0A | | | 2.0 | V |
| tf | Fall Time | Ic= 4A, I _{B1} = 0.8A; I _{B2} = -1.6A R _L = 50 Ω; V _{CC} = 200V | | | 0.4 | us |

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